Observation of current-induced spin polarization with different polarities in BiSbTeSe₂ topological insulators

Fan Yang, University of Cologne

Topological insulators (TIs) are a class of material which possess spin-momentum-locked Dirac Fermions on the surfaces. Due to the spin-momentum locking, when a charge current flows through the surface of a TI, a spin polarization will be induced, the polarity of which is determined by the spin texture of the surface states. Such current-induced spin polarization can be detected by using a ferromagnetic tunneling contact as a detector. In this talk, we present our data measured in devices fabricated from BiSbTeSe₂ flakes. An unexpected spin polarization with an opposite polarity was observed in low-carrier-density devices. Possible origins of the polarity change will be discussed.



BIO: Dr. Fan Yang earned his Ph.D. in condensed-matter physics at the Institution of Physics, Chinese Academy of Sciences, in 2012. He is currently a research fellow at the Institute of Physics II, University of Cologne, working with Prof. Yoichi Ando as an experimentalist on nano-devices and low-temperature transport measurement. His previous work mainly focused on devices based on three-dimensional topological insulators (TIs), such as TI-superconductor hybrid structures (Phys. Rev. B 85, 104508; Sci. Rep. 2, 339; Phys. Rev. B 86, 134504), gated TI devices (Phys. Rev. Lett. 105, 176602; Appl. Phys. Lett. 104, 161614; ACS Nano 9, 4050), TI interferometers (Phys. Rev. Lett. 107, 016802) and spintronic devices based on TI materials (Nano Lett 14, 6226).